

#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	Rds(ON) Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	7.5Ω @ V <sub>GS</sub> = 5V	0.23A

### **Features and Benefits**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
  - https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (2N7002DWQ)

### **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{\text{DS(ON)}})$  yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Power Management Functions

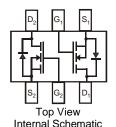
#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Lead-Frame (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

SOT363 (Standard)



Top View



#### **Ordering Information** (Note 4)

Part Number	Case	Packaging
2N7002DW-7-F	SOT363 (Standard)	3,000/Tape & Reel
2N7002DW-13-F	SOT363 (Standard)	10,000/Tape & Reel

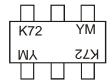
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

June 2021



## **Marking Information**



K72 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: I = 2021) M or  $\overline{M}$ = Month (ex: 9 = September)

#### Date Code Key

Year	2004		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	R		ı	J	K	L	M	N	0	Р	R	S
Month	lon	Feb	Mar	Anr	May	lun	Jul	Aug	Sep	Oct	Nov	Dec
WOTH	Jan	reb	IVIAI	Apr	iviay	Jun	Jui	Aug	Sep	OCI	NOV	Dec

## **Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	60	V		
Drain-Gate Voltage R <sub>G</sub> s ≤ 1.0MΩ			Vdgr	60	V
Gate-Source Voltage		Continuous	Vgss	±20	V
Gale-Source Vollage	F	Pulsed (Note 8)	Vgss	±40	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ $T_A = +100^{\circ}C$		0.23 0.18 0.14	А
Maximum Continuous Body Diode Forward Curre		ls	0.23	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle =	I <sub>DM</sub>	0.8	Α		

## Thermal Characteristics (@ TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
	T <sub>A</sub> = +25°C		0.31	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	$P_D$	0.2	W
	T <sub>A</sub> = +100°C		0.12	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	410	°C/W
	T <sub>A</sub> = +25°C		0.4	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	PD	0.25	W
	T <sub>A</sub> = +100°C		0.15	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	318	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	Rejc	135	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
   Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.



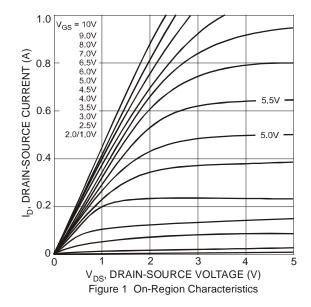
## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

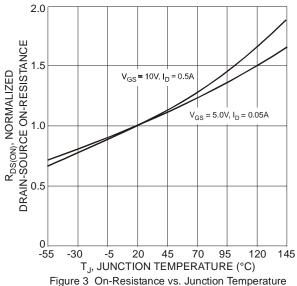
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BVDSS	60	70		٧	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	@ T <sub>C</sub> = +25°C @ T <sub>C</sub> = +125°C	IDSS	_	_	1.0 500	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage		Igss	_	_	±10	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V <sub>GS(TH)</sub>	1.0	_	2.0	٧	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
Static Drain-Source On-Resistance	@ T <sub>J</sub> = +25°C	RDS(ON)	_	3.2 4.4	7.5 13.5	Ω	$V_{GS} = 5.0V, I_{D} = 0.05A$
	@ $T_J = +125$ °C						$V_{GS} = 10V, I_{D} = 0.5A$
On-State Drain Current		I <sub>D(ON)</sub>	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		<b>g</b> FS	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage		VsD	_	0.78	1.5	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 115mA
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		Ciss	_	22	50	pF	
Output Capacitance		Coss	_	11	25	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	2.0	5.0	pF	1 = 1.0WH12
Turn-On Delay Time		tD(ON)	_	7.0	20		$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t <sub>D(OFF)</sub>	_	11.0	20	ns	$\begin{aligned} R_L &= 150\Omega, \ V_{GEN} = 10V, \\ R_{GEN} &= 25\Omega \end{aligned}$

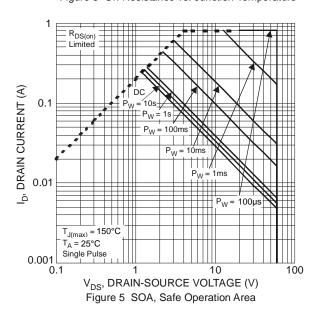
Notes:

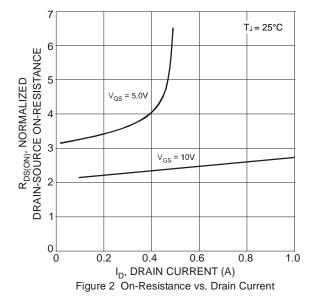
<sup>7.</sup> Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.

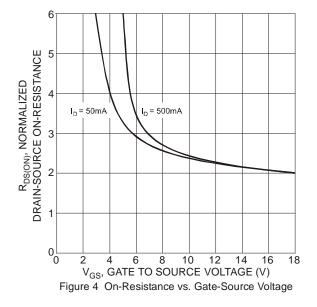








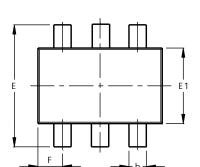


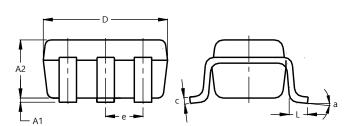




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.





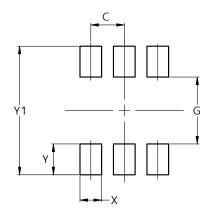
SC	SOT363 (Standard)							
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.80	1.00	0.90					
b	0.10	0.35	0.225					
С	0.08	0.22	0.15					
D	1.80	2.20	2.00					
Е	2.00	2.45	2.225					
E1	1.15	1.35	1.25					
е	-	1	0.65					
F	0.25	0.45	0.35					
L	0.25	0.46	0.355					
а	0°	8°						
All I	All Dimensions in mm							

## **Suggested Pad Layout**

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

#### SOT363 (Standard)

SOT363 (Standard)



Dimensions	Value		
Dillielisions	(in mm)		
С	0.650		
G	1.300		
Х	0.420		
Y	0.600		
Y1	2.500		



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